

SWIR Multichip Emitter & Detector

Product No: MTMD1479PD6T38

Peak Emission Wavelengths: 1460,1720,1900nm Detector Sensitivity Wavelength Range: 600-2600nm

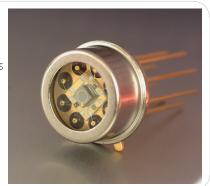
The MTMD1479PD6T38 is a SWIR multi-chip emitter with a InGaAs Photodiode designed for applications requiring various emission sources in a small, densley packaged area. These devices can be custom designed for specific wavelengths and outputs.

FEATURES

- > Hermetically Sealed TO-5 Metal Can Package
- > PIN Photodiode Chip Active Area: 1.0mm
- > High Output Power

APPLICATIONS

- > High Speed Communications
- > Medical / Chemical Analysis
- > Biofluorescense Analysis



Emitter Absolute Maximum Ratings (Ta=25°C)							RoHS
ITEMS	SYMBOL	RATINGS		UNIT			
		1460	1720	1900			
Forward Current (DC)	IF	50	50	50	mA		
Forward Current (Pulse) *1	IFP				А		
Reverse Voltage	VR	5	5	5	V		
Power Dissipation	PD	50	50	50	mW		
Operating Temperature Range	Topr	-)	20~+85		°C		
Storage Temperature Range	Tstg	-30~+100			°C		
Junction Temperature	Tj		100		°C		
Lead Soldering Temperature *2	Tls		260		°C		
			*1: Tw=	10usec. T=1	0msec. *2: Time 5 Sec max; P	osition: Up to 3mm fr	om the body

Emitter Electrical & Optical Characteristics (Ta=25°C)								
ITEMS	SYMBOL	WAVELENGTH	CONDITIONS	MIN	TYP	MAX	UNIT	
Forward Voltage	VF	1460	IF=50mA		1.02		V	
Forward Voltage	VF	1720	IF=50mA		0.096		V	
Forward Voltage	VF	1900	IF=50mA		0.090		V	
Reverse Current	IR		VR=5V			10	uA	
Power Output	PO	1460	IF=50mA		2.9		mW	
Power Output	PO	1720	IF=50mA		2.3		mW	
Power Output	PO	1900	IF=50mA		1.9		mW	

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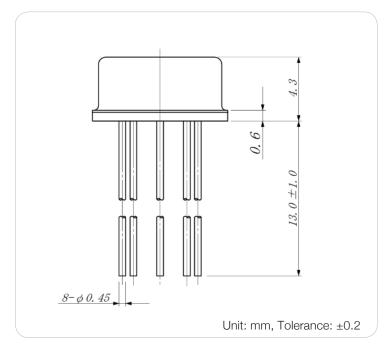


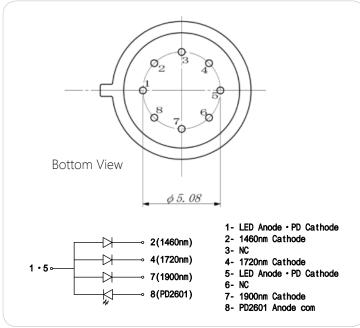
Emitter Electrical	& Optical	Characterist	tics (Ta=25°C)				
ITEMS	SYMBOL	WAVELENGTH	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Emission Wavelength	ур	1460	IF=50mA		1460		nm
Peak Emission Wavelength	λр	1720	IF=50mA		1741		nm
Peak Emission Wavelength	λр	1900	IF=50mA		1893		nm
Spectral Line Half Width	Δλ	1460	IF=50mA		107		nm
Spectral Line Half Width	Δλ	1720	IF=50mA		141		nm
Spectral Line Half Width	Δλ	1900	IF=50mA		160		nm

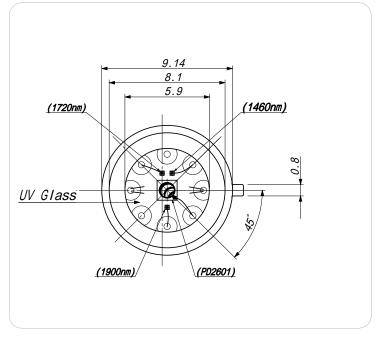
Detector Electric	al & Optica	al Charactei	ristics (Ta = 2	25°C)	
ITEMS	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Breakdown Voltage	VR	IR=100uA			1	V
Sensitivity Range	λ	VR=0V	600		2600	nm
Dark Current	ID	VR=1V			300	uA
Capacitance	C	VR=0V		1000		pF
Capacitance	C	VR=1V		85		pF
Responsivity	R	λ=2400nm		1.24		A/W
Shunt Resistance	RS	VR=10mV		3.3		MOhm
Quantum Efficiency	QE	λ=1840nm		72		%
Light Current @1300nm	IL	If=10mA		30		uA
Light Current @1300nm	IL	If=20mA		65		uA





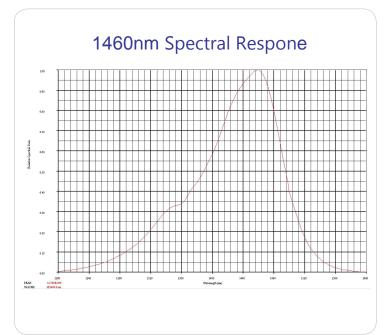


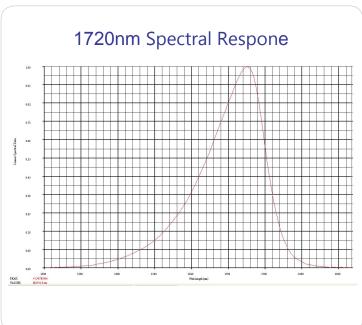


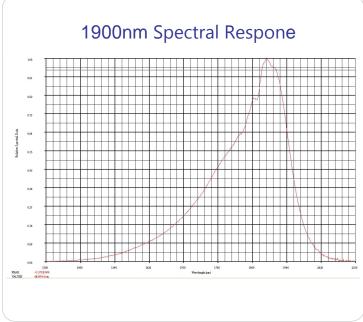




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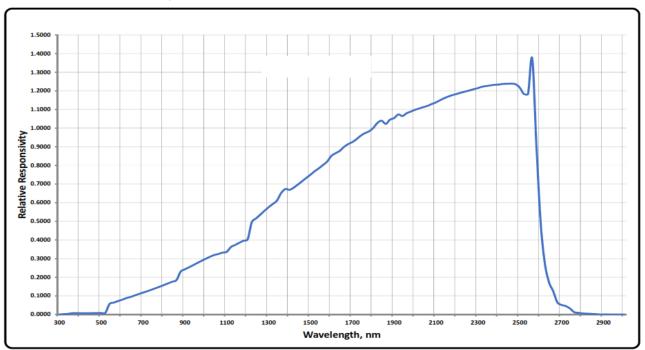


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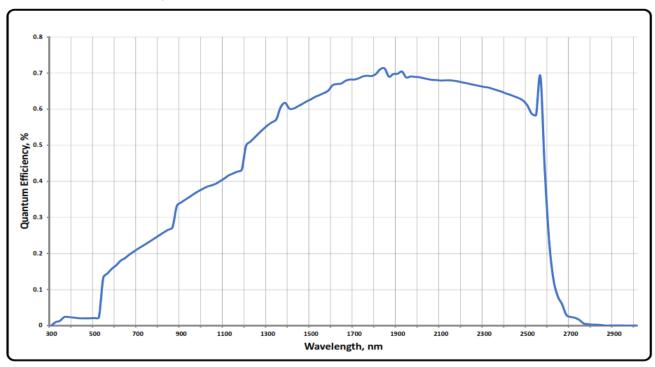




Spectral Responsivity



Quantum Efficiency



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